

S10 8	119	S107 and bottom adj electrode	US-PGPUB; USPAT; USOCR; JPO	AND	OFF	2004/12/16 15:17
S10 9	89	S108 and top adj electrode	US-PGPUB; USPAT; USOCR; JPO	AND	OFF	2004/12/16 15:45
S11 0	998	capacitor with structure.ti.	US-PGPUB; USPAT; USOCR; JPO	AND	OFF	2004/12/16 15:46
S11 1	177	S110 and(high adj dielectric)	US-PGPUB; USPAT; USOCR; JPO	AND	OFF	2004/12/16 16:41
S11 2	2287	semiconductor adj device.ti. and(high adj dielectric)	US-PGPUB; USPAT; USOCR; JPO	AND	OFF	2004/12/16 16:41
S11 3	1785	S112 and electrode	US-PGPUB; USPAT; USOCR; JPO	AND	OFF	2004/12/16 16:42
S11 4	1227	S112 and capacitor	US-PGPUB; USPAT; USOCR; JPO	AND	OFF	2004/12/16 16:42
S11 5	1152	S113 and S114	US-PGPUB; USPAT; USOCR; JPO	AND	OFF	2004/12/16 16:42
S11 6	391	S115 and insulating adj layer	US-PGPUB; USPAT; USOCR; JPO	AND	OFF	2004/12/17 09:06
S11 7	10	"5923062"	US-PGPUB; USPAT; USOCR; JPO	AND	OFF	2004/12/17 10:40
S11 8	17965	semiconductor with device.ti. and capacitor	US-PGPUB; USPAT; USOCR; JPO	AND	OFF	2004/12/17 10:41
S11 9	3685	S118 and(insulat\$3 with silicon adj oxide)	US-PGPUB; USPAT; USOCR; JPO	AND	OFF	2004/12/17 10:42

S12 0	1842	S119 and(transistor with electrode)	US-PGPUB; USPAT; USOCR; JPO	AND	OFF	2004/12/17 10:42
S12 1	4	S120 and(TiO2)	US-PGPUB; USPAT; USOCR; JPO	AND	OFF	2004/12/17 10:43
S12 2	569	S120 and(dielectric adj constant)	US-PGPUB; USPAT; USOCR; JPO	AND	OFF	2004/12/17 10:44
S12 3	43	S120 and(dielectric adj constant adj higher)	US-PGPUB; USPAT; USOCR; JPO	AND	OFF	2004/12/17 10:44